Advance Information

Low-Voltage 1.8/2.5/3.3V 16-Bit Transceiver

With 26 Ω Series Resisters on A and B Outputs and 3.6 V–Tolerant Inputs and Outputs (3–State, Non–Inverting)

The 74 VCXR 162245 is an advanced performance, non-inverting 16-bit transceiver. It is designed for very high-speed, very low-power operation in 1.8 V, 2.5 V or 3.3 V systems.

When operating at 2.5 V (or 1.8 V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3 V busses. It is guaranteed to be over–voltage tolerant to 3.6 V.

The VCXR162245 is designed with byte control. It can be operated as two separate octals, or with the controls tied together, as a 16–bit wide function. It is designed with 26 Ω series resistors in each of the A and B outputs to reduce noise. The Transmit/Receive (T/Rn) inputs determine the direction of data flow through the bi–directional transceiver. Transmit (active–HIGH) enables data from A ports to B ports; Receive (active–LOW) enables data from B to A ports. The Output Enable inputs (\overline{OEn}), when HIGH, disable both A and B ports by placing them in a HIGH Z condition.

- Designed for Low Voltage Operation: $V_{CC} = 1.65-3.6 \text{ V}$
- 3.6 V Tolerant Inputs and Outputs
- 26 Ω Series Resistors on All Outputs
- High Speed Operation: 3.4 ns max for 3.0 to 3.6 V

4.3 ns max for 2.3 to 2.7 V 8.6 ns max for 1.65 to 1.95 V

• Static Drive: ±24 mA Drive at 3.0 V

±18 mA Drive at 2.3 V ±3 mA Drive at 1.65 V

- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- Near Zero Static Supply Current in All Three Logic States (20 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±300 mA @ 125°C
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



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TSSOP-48 DT SUFFIX CASE 1201

MARKING DIAGRAM

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A = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

PIN NAMES

Pins	Function
OEn	Output Enable Inputs
T/Rn	Transmit/Receive Inputs
A0–A15	Side A Inputs or 3–State Outputs
B0–B15	Side B Inputs or 3–State Outputs

ORDERING INFORMATION

Device	Package	Shipping
74VCXR162245DT	TSSOP	39 / Rail
74VCXR162245DTR	TSSOP	2500 / Reel

This document contains information on a new product. Specifications and information herein are subject to change without notice.

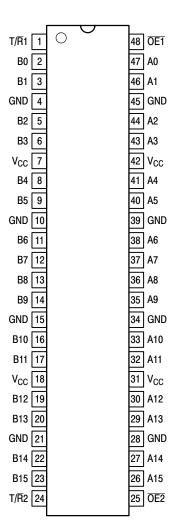


Figure 1. 48-Lead Pinout (Top View)

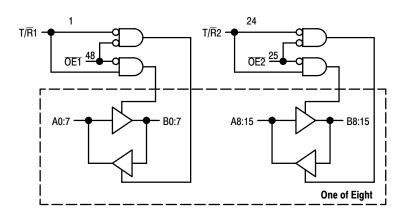
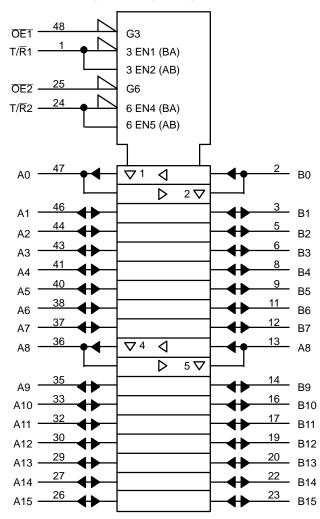


Figure 2. Logic Diagram



Inp	uts	Outputo	Inputs		Outputo
OE1	T/R1	Outputs	OE2	T/R2	Outputs
L	L	Bus B0:7 Data to Bus A0:7	L	L	Bus B8:15 Data to Bus A8:15
L	Н	Bus A0:7 Data to Bus B0:7	L	Н	Bus A8:15 Data to Bus B8:15
Н	Х	High Z State on A0:7, B0:7	Н	Х	High Z State on A8:15, B8:15

H = High Voltage Level; L = Low Voltage Level; X = High or Low Voltage Level and Transitions Are Acceptable

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +4.6$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +4.6$	Output in 3–State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Note 1.; Outputs Active	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	- 50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.2	3.3 3.3	3.6 3.6	V
VI	Input Voltage		-0.3		3.6	V
V _O	Output Voltage	(Active State) (3–State)	0 0		V _{CC} 3.6	V

A Outputs

I _{OH}	HIGH Level Output Current, V _{CC} = 3.0V – 3.6V		-12	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 3.0V - 3.6V$		12	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.3V – 2.7V		-8	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.3V - 2.7V		8	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 1.65 – 1.95V		-4	mA
I _{OL}	LOW Level Output Current, V _{CC} = 1.65 – 1.95V		4	mA

B Outputs

I _{OH}	HIGH Level Output Current, V _{CC} = 3.0V – 3.6V		-12	mA
I _{OL}	LOW Level Output Current, V _{CC} = 3.0V – 3.6V		12	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.3V – 2.7V		-8	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.3V – 2.7V		8	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 1.65 – 1.95V		-4	mA
I _{OL}	LOW Level Output Current, V _{CC} = 1.65 – 1.95V		4	mA
T _A	Operating Free–Air Temperature	-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8V to 2.0V, V_{CC} = 3.0V	0	10	ns/V

^{1.} I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°0	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	1.65V ≤ V _{CC} < 2.3V	0.7 x V _{CC}		V
		2.3V ≤ V _{CC} ≤ 2.7V	1.6		1
		2.7V < V _{CC} ≤ 3.6V	2.0		1
V _{IL}	LOW Level Input Voltage (Note 2.)	1.65V ≤ V _{CC} < 2.3V		0.3 x V _{CC}	V
		2.3V ≤ V _{CC} ≤ 2.7V		0.7	1
		2.7V < V _{CC} ≤ 3.6V		0.8	1
V _{OH}	HIGH Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; I_{OH} = -100\mu A$	V _{CC} - 0.2		V
		V _{CC} = 1.65V; I _{OH} = -3mA	1.4		1
		$V_{CC} = 2.3V; I_{OH} = -4mA$	2.0		1
		$V_{CC} = 2.3V; I_{OH} = -6mA$	1.8		1
		$V_{CC} = 2.3V; I_{OH} = -8mA$	1.7		1
		$V_{CC} = 2.7V; I_{OH} = -6mA$	2.2		1
		$V_{CC} = 3.0V; I_{OH} = -8mA$	2.4		1
		$V_{CC} = 3.0V; I_{OH} = -12mA$	2.2		1
V _{OL}	LOW Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; I_{OL} = 100\mu A$		0.2	V
		V _{CC} = 1.65V; I _{OL} = 3mA		0.3	1
		V _{CC} = 2.3V; I _{OL} = 6mA		0.4	
		V _{CC} = 2.3V; I _{OL} = 8mA		0.6	1
		V _{CC} = 2.7V; I _{OL} = 6mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 8mA		0.55	
		V _{CC} = 3.0V; I _{OL} = 12mA		0.8	
II	Input Leakage Current	$1.65V \le V_{CC} \le 3.6V; \ 0V \le V_{I} \le 3.6V$		±5.0	μΑ
I _{OZ}	3-State Output Current	$1.65V \le V_{CC} \le 3.6V$; $0V \le V_O \le 3.6V$; $V_I = V_{IH}$ or V_{IL}		±10	μА
I _{OFF}	Power-Off Leakage Current	$V_{CC} = 0V$; V_I or $V_O = 3.6V$		10	μΑ
I _{CC}	Quiescent Supply Current (Note 3.)	$1.65V \le V_{CC} \le 3.6V$; $V_I = GND$ or V_{CC}		20	μΑ
		$1.65V \le V_{CC} \le 3.6V; 3.6V \le V_I, V_O \le 3.6V$		±20	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.7V < V_{CC} \le 3.6V; V_{IH} = V_{CC} - 0.6V$		750	μΑ

These values of V_I are used to test DC electrical characteristics only.
 Outputs disabled or 3-state only.

AC CHARACTERISTICS (Note 4.; $t_R = t_F = 2.0$ ns; $C_L = 30$ pF; $R_L = 500\Omega$)

					Lir	mits			
					T _A = -40°	C to +85°C			
			V _{CC} = 3.0	OV to 3.6V	V _{CC} = 2.3	3V to 2.7V	V _{CC} = 1.6	65 to1.95V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output (A > B)	1	0.8 0.8	3.4 3.4	1.0 1.0	4.3 4.3	1.5 1.5	5.7 5.7	ns
t _{PLH} t _{PHL}	Propagation Delay Input to Output (B > A)	1	0.8 0.8	3.4 3.4	1.0 1.0	4.3 4.3	1.5 1.5	5.7 5.7	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level (A > B)	2	0.8 0.8	4.2 4.2	1.0 1.0	5.7 5.7	1.5 1.5	7.6 7.6	ns
t _{PZH}	Output Enable Time to High and Low Level (B > A)	2	0.8 0.8	4.2 4.2	1.0 1.0	5.7 5.7	1.5 1.5	7.6 7.6	ns
t _{PHZ}	Output Disable Time From High and Low Level (A > B)	2	0.8 0.8	4.1 4.1	1.0 1.0	4.8 4.8	1.5 1.5	5.7 5.7	ns
t _{PHZ}	Output Disable Time From High and Low Level (B > A)	2	0.8 0.8	4.1 4.1	1.0 1.0	4.8 4.8	1.5 1.5	5.7 5.7	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 5.)			0.5 0.5		0.5 0.5		0.5 0.5	ns

^{4.} For $C_L = 50 pF$, add approximately 300ps to the AC maximum specification.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
V _{OLP}	Dynamic LOW Peak Voltage	$V_{CC} = 1.8V, C_L = 30pF, V_{IH} = V_{CC}, V_{IL} = 0V$	0.15	V
	(Note 6.)	V_{CC} = 2.5V, C_L = 30pF, V_{IH} = V_{CC} , V_{IL} = 0V	0.25	7
		V_{CC} = 3.3V, C_L = 30pF, V_{IH} = V_{CC} , V_{IL} = 0V	0.35	7
V _{OLV}	Dynamic LOW Valley Voltage	$V_{CC} = 1.8V, C_L = 30pF, V_{IH} = V_{CC}, V_{IL} = 0V$	-0.15	V
	(Note 6.)	V_{CC} = 2.5V, C_L = 30pF, V_{IH} = V_{CC} , V_{IL} = 0V	-0.25	7
		V_{CC} = 3.3V, C_L = 30pF, V_{IH} = V_{CC} , V_{IL} = 0V	-0.35	
V _{OHV}	Dynamic HIGH Valley Voltage	$V_{CC} = 1.8V, C_L = 30pF, V_{IH} = V_{CC}, V_{IL} = 0V$	1.55	V
	(Note 7.)	V_{CC} = 2.5V, C_L = 30pF, V_{IH} = V_{CC} , V_{IL} = 0V	2.05	7
		$V_{CC} = 3.3V, C_L = 30pF, V_{IH} = V_{CC}, V_{IL} = 0V$	2.65	

^{6.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

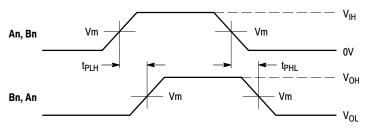
Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

^{7.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the HIGH state.

CAPACITIVE CHARACTERISTICS

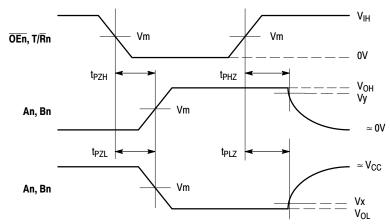
Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	Note 8.	6	pF
C _{OUT}	Output Capacitance	Note 8.	7	pF
C _{PD}	Power Dissipation Capacitance	Note 8., 10MHz	20	pF

8. $V_{CC} = 1.8$, 2.5 or 3.3V; $V_I = 0V$ or V_{CC} .



WAVEFORM 1 - PROPAGATION DELAYS

 t_R = t_F = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns

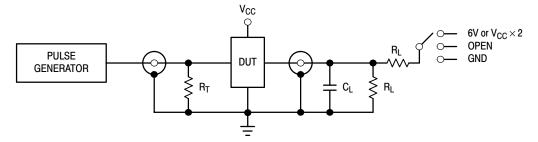


WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 t_R = t_F = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns

Figure 3. AC Waveforms

	V _{CC}				
Symbol	3.3V ±0.3V	2.5V ±0.2V	1.8V ±0.15V		
V _{IH}	2.7V	V _{CC}	V _{CC}		
V _m	1.5V	V _{CC} /2	V _{CC} /2		
V _x	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V		
V _y	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V		

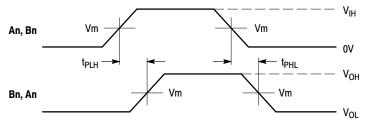


TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V at $V_{CC} = 3.3 \pm 0.3V$; $V_{CC} \times 2$ at $V_{CC} = 2.5 \pm 0.2V$; 1.8V $\pm 0.15V$
t _{PZH} , t _{PHZ}	GND

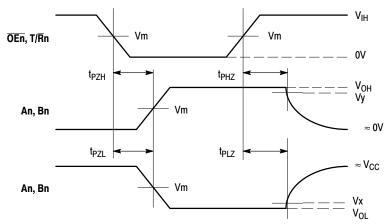
 C_L = 30pF or equivalent (Includes jig and probe capacitance) R_L = 500Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit



 $\label{eq:waveform 3 - PROPAGATION DELAYS} t_R = t_F = 2.0 ns, 10\% \ to \ 90\%; \ f = 1 MHz; \ t_W = 500 ns$

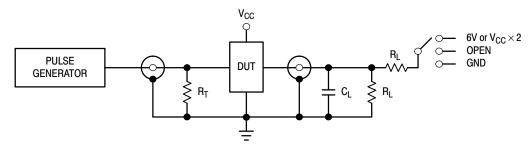


WAVEFORM 4 - OUTPUT ENABLE AND DISABLE TIMES

 t_R = t_F = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns

Figure 5. AC Waveforms

	V _{CC}			
Symbol	3.3V ±0.3V 2.7V			
V _{IH}	2.7V	2.7V		
V _m	1.5V	1.5V		
V _x	V _{OL} + 0.3V	V _{OL} + 0.3V		
V _y	V _{OH} – 0.3V	V _{OH} – 0.3V		



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V at V_{CC} = 3.3 ±0.3V; $V_{CC} \times$ 2 at V_{CC} = 2.5 ±0.2V; 1.8 ±0.15V
t _{PZH} , t _{PHZ}	GND

 C_L = 50pF or equivalent (Includes jig and probe capacitance)

 $R_L = 500\Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

AC CHARACTERISTICS ($t_R = t_F = 2.0 ns; C_L = 50 pF; R_L = 500 \Omega$)

				Limits				
ı			T _A = -40°C to +85°C				1	
				V _{CC} = 3.	0V to 3.6V	V _{CC} :	V _{CC} = 2.7V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit	
t _{PLH}	Propagation Delay Input to Output	(A > B)	3	1.0 1.0	4.2 4.2		4.7 4.7	ns
t _{PLH}	Propagation Delay Input to Output	(B > A)	3	1.0 1.0	4.2 4.2		4.7 4.7	ns
t _{PZH}	Output Enable Time to High and Low Level	(A > B)	4	1.0 1.0	5.6 5.6		6.7 6.7	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	(B > A)	4	1.0 1.0	5.6 5.6		6.7 6.7	ns
t _{PHZ}	Output Disable Time From High and Low Level	(A > B)	4	1.0 1.0	5.5 5.5		5.7 5.7	ns
t _{PHZ}	Output Disable Time From High and Low Level	(B > A)	4	1.0 1.0	5.5 5.5		5.7 5.7	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 9.)				0.5 0.5		0.5 0.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

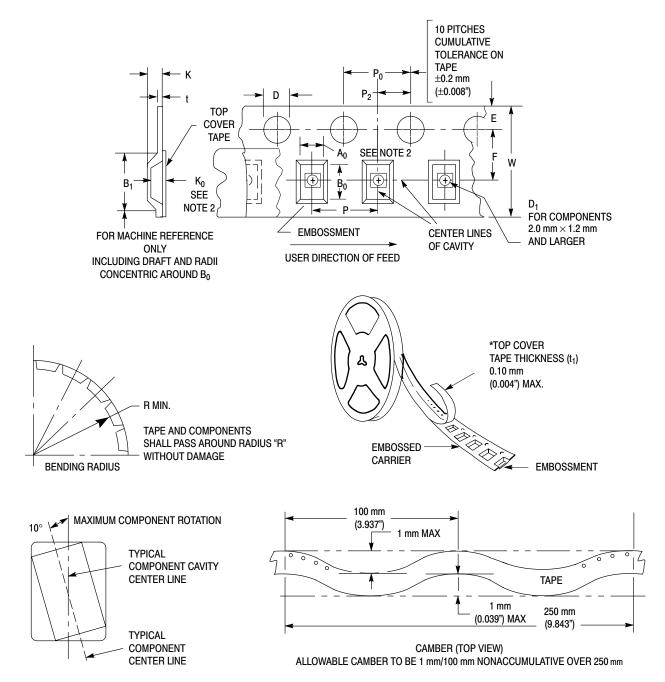


Figure 7. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B ₁ Max	D	D ₁	E	F	к	Р	P ₀	P ₂	R	Т	w
24mm	20.1mm (0.791")	1.5 + 0.1mm -0.0 (0.059 +0.004" -0.0)	1.5mm Min (0.060")	1.75 ±0.1 mm (0.069 ±0.004")	11.5 ±0.10 mm (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 ±0.1 mm (0.63 ±0.004")	4.0 ±0.1 mm (0.157 ±0.004")	2.0 ±0.1 mm (0.079 ±0.004")	30 mm (1.18")	0.6 mm (0.024")	24.3 mm (0.957")

^{1.} Metric Dimensions Govern-English are in parentheses for reference only.

^{2.} A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

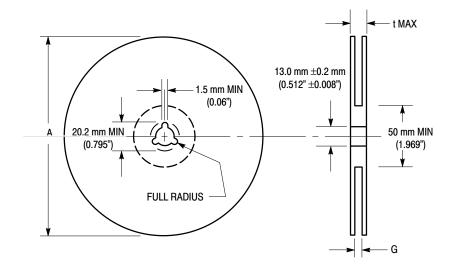


Figure 8. Reel Dimensions

REEL DIMENSIONS

Tape Size	A Max	G	t Max
24 mm	360 mm	24.4 mm + 2.0 mm, -0.0	30.4 mm
	(14.173")	(0.961" + 0.078", -0.00)	(1.197")

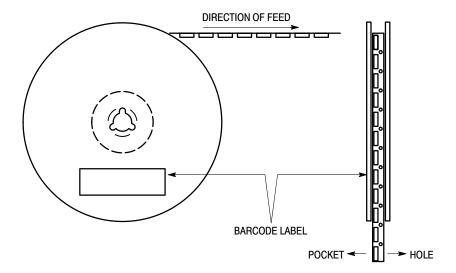


Figure 9. Reel Winding Direction

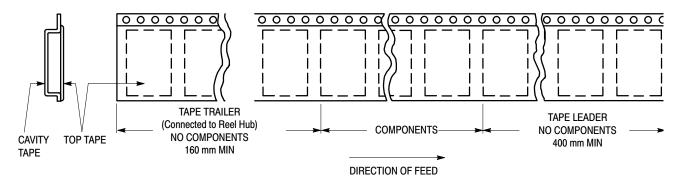


Figure 10. Tape Ends for Finished Goods

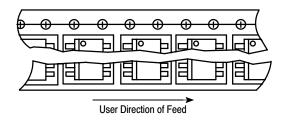
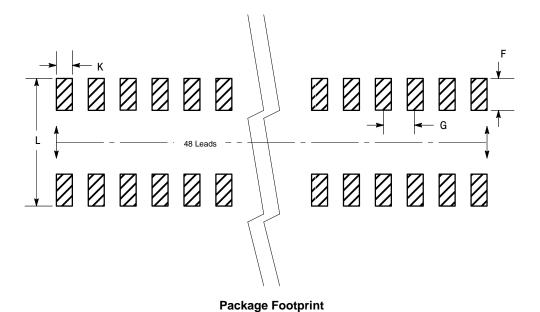
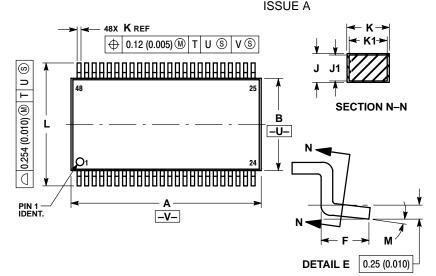


Figure 11. Reel Configuration



PACKAGE DIMENSIONS

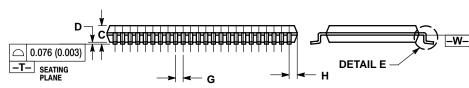
TSSOP DT SUFFIX CASE 1201–01



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION K DOES NOT INCLUDE DAMBAR
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- REFERENCE ONLY.
 6. DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN MAX		MIN	MAX
Α	12.40	12.60	0.488	0.496
В	6.00	6.20	0.236	0.244
C		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.50 BSC		0.019	7 BSC
Н	0.37		0.015	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.17	0.27	0.007	0.011
K1	0.17	0.23	0.007	0.009
L	7.95	8.25	0.313	0.325
M	0 °	8 °	0 °	8 °



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